

AON5800

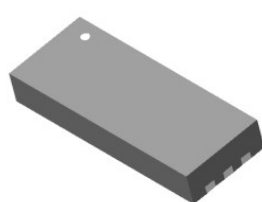
Common-Drain Dual N-Channel Enhancement Mode Field Effect Transistor

General Description

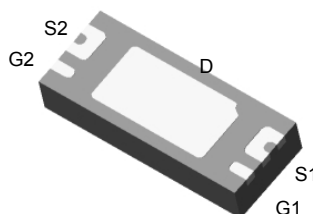
The AON5800 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 1.8V while retaining a 12V $V_{GS(MAX)}$ rating. It is ESD protected. This device is suitable for use as a uni-directional or bi-directional load switch, facilitated by its common-drain configuration. *Standard Product AON5800 is Pb-free (meets ROHS & Sony 259 specifications). AON5800L is a Green Product ordering option. AON5800 and AON5800L are electrically identical.*

Features

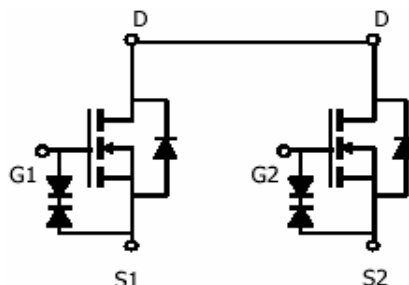
$V_{DS} (V) = 20V$
 $I_D = 8 A \quad (V_{GS} = 10V)$
 $R_{DS(ON)} < 16 m\Omega \quad (V_{GS} = 10V)$
 $R_{DS(ON)} < 20 m\Omega \quad (V_{GS} = 4.5V)$
 $R_{DS(ON)} < 21 m\Omega \quad (V_{GS} = 4.0V)$
 $R_{DS(ON)} < 22 m\Omega \quad (V_{GS} = 3.1V)$
 $R_{DS(ON)} < 27 m\Omega \quad (V_{GS} = 2.5V)$
 $R_{DS(ON)} < 45 m\Omega \quad (V_{GS} = 1.8V)$
ESD Rating: 2000V HBM



Top View



Bottom View



Absolute Maximum Ratings $T_A=25^\circ C$ unless otherwise noted

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	± 12	
Continuous Drain Current $T_A=25^\circ C$	I_D	8	A
Current $R_{\theta JA}=75^\circ C/W$ $T_A=70^\circ C$		6.3	
Pulsed Drain Current ^C	I_{DM}	45	
Power Dissipation ^A $T_A=25^\circ C$	P_{DSM}	1.6	W
$R_{\theta JA}=75^\circ C/W$ $T_A=70^\circ C$		1.0	
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	$^\circ C$

Thermal Characteristics

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A $t \leq 10s$	$R_{\theta JA}$	30	40	$^\circ C/W$
Maximum Junction-to-Ambient ^A Steady-State		61	75	$^\circ C/W$
Maximum Junction-to-Case ^B Steady-State	$R_{\theta JC}$	4.5	6	$^\circ C/W$

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV _{DSS}	Drain-Source Breakdown Voltage	I _D =250μA, V _{GS} =0V	20			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =16V, V _{GS} =0V T _J =55°C			1 5	μA
I _{GSS}	Gate-Body leakage current	V _{DS} =0V, V _{GS} =±10V			10	μA
BV _{GSO}	Gate-Source Breakdown Voltage	V _{DS} =0V, I _G =±250uA	±12			V
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	0.5	0.73	1	V
I _{D(ON)}	On state drain current	V _{GS} =10V, V _{DS} =5V	30			A
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =10V, I _D =8A T _J =125°C		13 18	16 22	mΩ
		V _{GS} =4.5V, I _D =7A		16	20	mΩ
		V _{GS} =4.0V, I _D =6A		17	21	mΩ
		V _{GS} =3.1V, I _D =6A		18	22	mΩ
		V _{GS} =2.5V, I _D =6A		22	27	mΩ
		V _{GS} =1.8V, I _D =4.5A		35	45	mΩ
g _{FS}	Forward Transconductance	V _{DS} =5V, I _D =8A		28		S
V _{SD}	Diode Forward Voltage	I _S =1A, V _{GS} =0V	0.5	0.74	1	V
I _S	Maximum Body-Diode Continuous Current				2.5	A
DYNAMIC PARAMETERS						
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =10V, f=1MHz		1330		pF
C _{oss}	Output Capacitance			182		pF
C _{rss}	Reverse Transfer Capacitance			161		pF
R _g	Gate resistance	V _{GS} =0V, V _{DS} =0V, f=1MHz		1.5		Ω
SWITCHING PARAMETERS						
Q _g (4.5V)	Total Gate Charge	V _{GS} =4.5V, V _{DS} =10V, I _D =8A		13.1		nC
Q _{gs}	Gate Source Charge			2		nC
Q _{gd}	Gate Drain Charge			3.9		nC
t _{D(on)}	Turn-On DelayTime	V _{GS} =5V, V _{DS} =10V, R _L =1.25Ω, R _{GEN} =3Ω		6.2		ns
t _r	Turn-On Rise Time			11		ns
t _{D(off)}	Turn-Off DelayTime			40.5		ns
t _f	Turn-Off Fall Time			10		ns
t _{rr}	Body Diode Reverse Recovery Time	I _F =8A, dI/dt=100A/μs		18.8		ns
Q _{rr}	Body Diode Reverse Recovery Charge	I _F =8A, dI/dt=100A/μs		8.1		nC

A: The value of R_{θJA} is measured with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The value in any given application depends on the user's specific board design. The current rating is based on the t ≤ 10s thermal resistance rating.

B: Repetitive rating, pulse width limited by junction temperature.

C: The R_{θJA} is the sum of the thermal impedance from junction to lead R_{θJL} and lead to ambient.

D: The static characteristics in Figures 1 to 6 are obtained using 80 μs pulses, duty cycle 0.5% max.

E: These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The SOA curve provides a single pulse rating.

Rev 6: Dec. 2005

THIS PRODUCT HAS BEEN DESIGNED AND QUALIFIED FOR THE CONSUMER MARKET. APPLICATIONS OR USES AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS ARE NOT AUTHORIZED. AOS DOES NOT ASSUME ANY LIABILITY ARISING OUT OF SUCH APPLICATIONS OR USES OF ITS PRODUCTS. AOS RESERVES THE RIGHT TO IMPROVE PRODUCT DESIGN, FUNCTIONS AND RELIABILITY WITHOUT NOTICE.

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

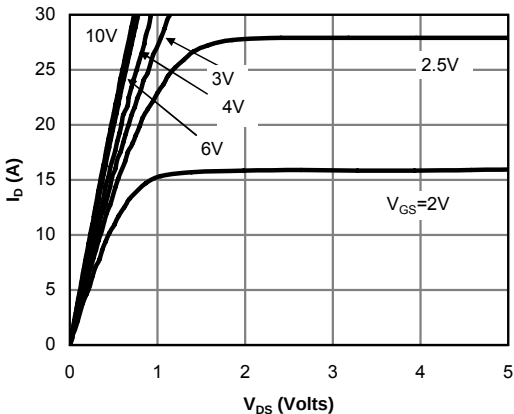


Fig 1: On-Region Characteristics

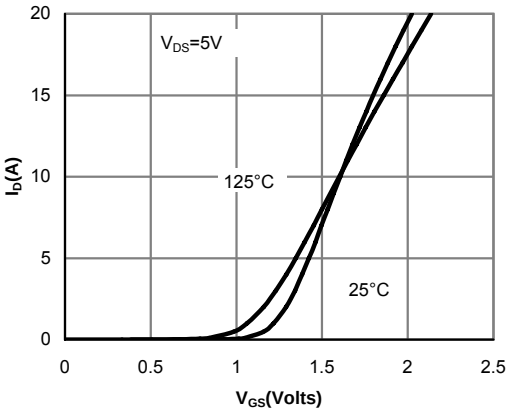


Figure 2: Transfer Characteristics

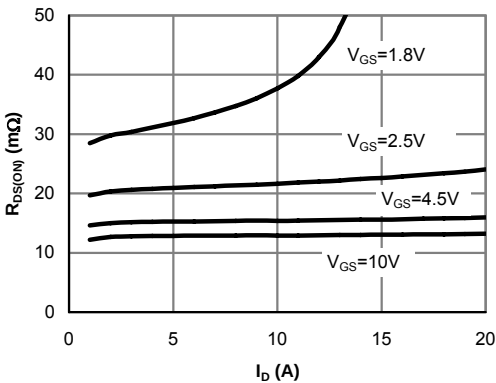


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

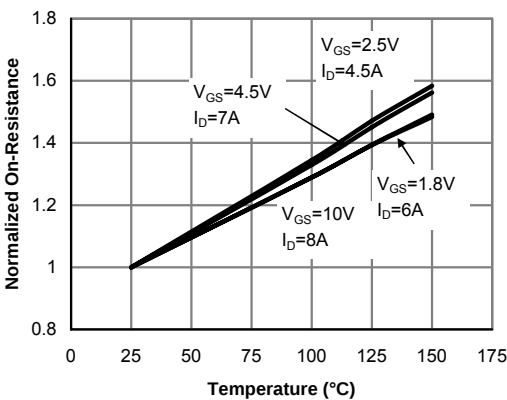


Figure 4: On-Resistance vs. Junction Temperature

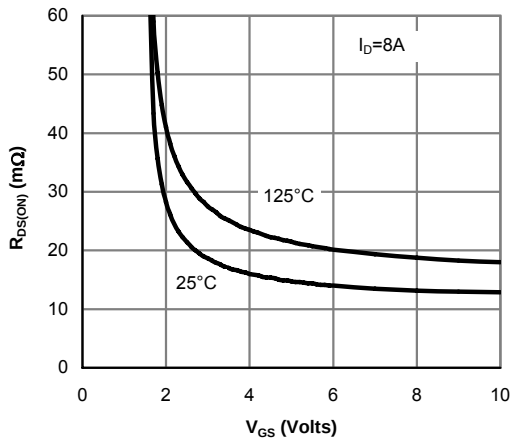


Figure 5: On-Resistance vs. Gate-Source Voltage

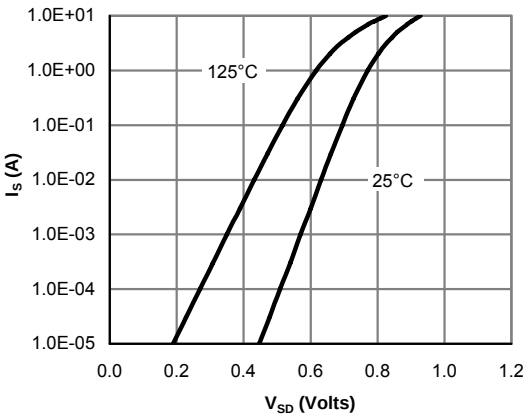


Figure 6: Body-Diode Characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

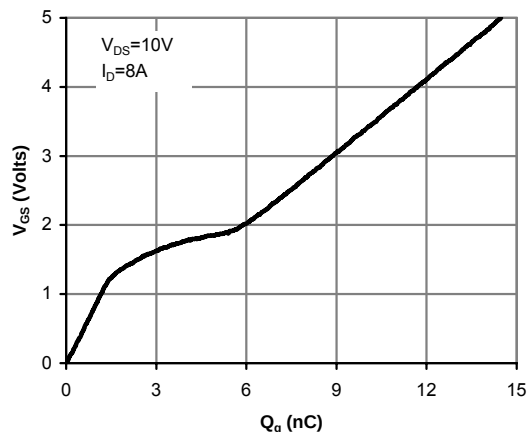


Figure 7: Gate-Charge Characteristics

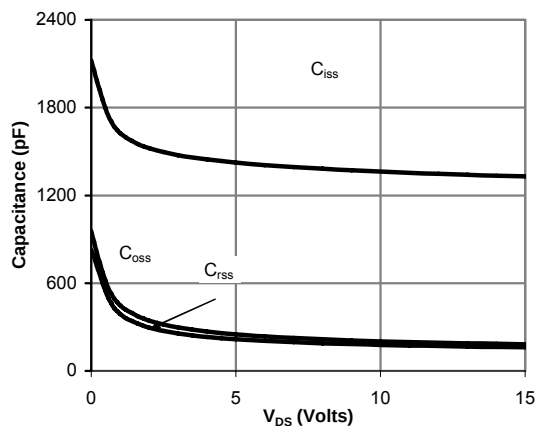


Figure 8: Capacitance Characteristics

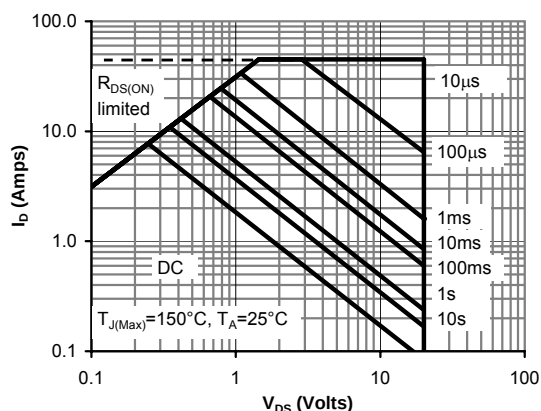


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

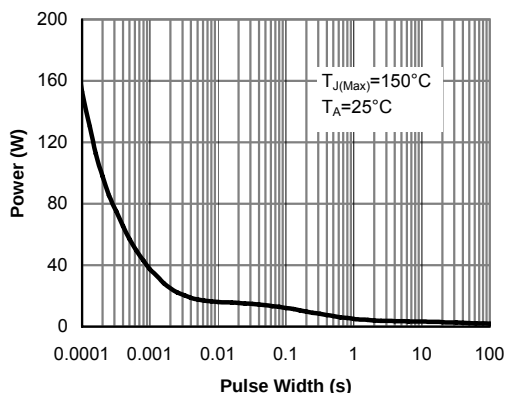


Figure 10: Single Pulse Power Rating Junction-to-Case (Note E)

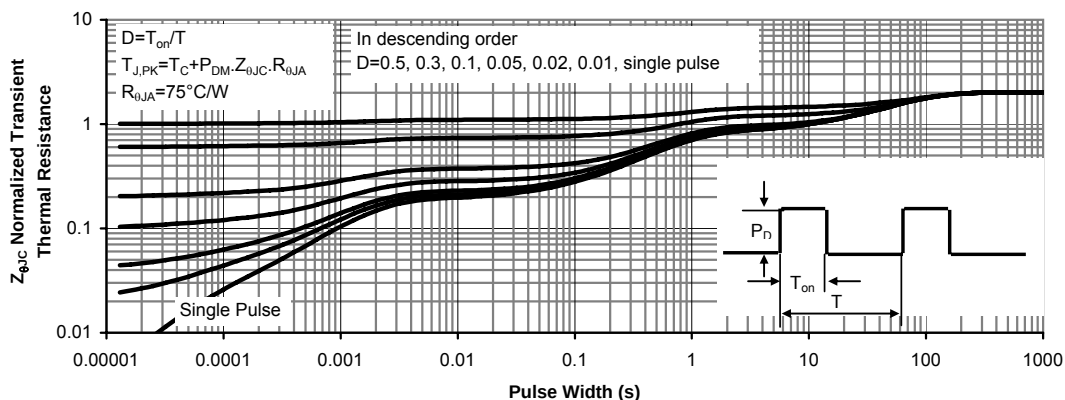


Figure 11: Normalized Maximum Transient Thermal Impedance (Note E)